Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	2624	(365/185.05,185.12,185.17,185. 21,185.23).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:58
L6	1	"5698879".PN.	USPAT; USOCR	OR	OFF	2005/03/17 13:59
L7	1	"4816883".PN.	USPAT; USOCR	OR	OFF	2005/03/17 13:59
L9	1	"5936887".PN.	USPAT; USOCR	OR	OFF	2005/03/17 13:59
L10	1	"6147911".PN.	USPAT; USOCR	OR	OFF	2005/03/17 14:00
L11	1	"20030094635".PN.	US-PGPUB	OR	OFF	2005/03/17 14:01
L12	1	"20030094635".PN.	US-PGPUB	OR	OFF	2005/03/17 14:05
S1	1	10/643876	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:23
S2	3816	(257/314-316).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/16 14:25
S3	3906	(438/257-265).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/16 14:25
S4	71391	flash near memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/16 14:26
S5	73618	flash near memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:26
S6	18962	polysilicon near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:26

S7	0	S6 near5 memor near cell near array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:27
S8	14	S6 near5 memory near cell near array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:33
S9	6330	select near transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:28
S10	6855870	S9 near5 wire connect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:29
S11	9	S9 near5 wire near connect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 15:49
S12	1	S11 near5 memory near cell near array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:29
S13	2	S6 near5 perpendicular near5 memory near cell near array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:35
S14	0	S11 near5 perpendicular near5 memory near cell near array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:35
S15	0	S11 with perpendicular near5 memory near cell near array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:35
S16	1	S11 and perpendicular near5 memory near cell near array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:35

S17	7	S5 and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 15:49
S18	1	symmetric near select near2 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:08
S19	73953	flash near memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 07:46
S20	2136	S19 and select near2 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 07:46
S21	360	S19 with select near2 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 07:47
S22	36	S21 and (select near2 transistor) with polysilicon near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:39
S23	7	S21 and (select near2 transistor) with polysilicon near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:02
S24	14	S19 and (select near2 transistor) with polysilicon near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:02
S25	7	S24 not S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:02
S26	8	symmetric near5 select near2 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:09

S27		4	S19 and S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:30
S28		4	S26 not S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:39
S29		1	S21 and (select near2 transistor) with ((polysilicon near5 gate) with (perpendicular near5 memory adj cell near2 array))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:41
S30		1	S19 and (select near2 transistor) with ((polysilicon near5 gate) with (perpendicular near5 memory adj cell near2 array))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:42
S31		1	S19 and (select near2 transistor) with ((polysilicon near5 gate) same(perpendicular near5 memory adj cell near2 array))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:42
S32		1	S19 and (select near2 transistor) with ((polysilicon near5 gate) same (perpendicular near5 memory adj cell near2 array))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:42
S33		1	S19 and (select near2 transistor) with ((polysilicon near5 gate) and (perpendicular near5 memory adj cell near2 array))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:42
S34		3	S19 and (select near2 transistor) with ((polysilicon near5 gate) and (perpendicular near5 memory adj cell))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 08:43
S35		6	S19 and (select near2 transistor) with (perpendicular near5 memory adj cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 09:35
S36		1	S19 and ((select near2 transistor) near5 extend$3) with (perpendicular near5 memory adj cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 09:36

S37	1	((select near2 transistor) near5 extend$3) with (perpendicular near5 memory adj cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 09:36
S38	3	((select near2 transistor) with extend$3) with (perpendicular near5 memory adj cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 09:36